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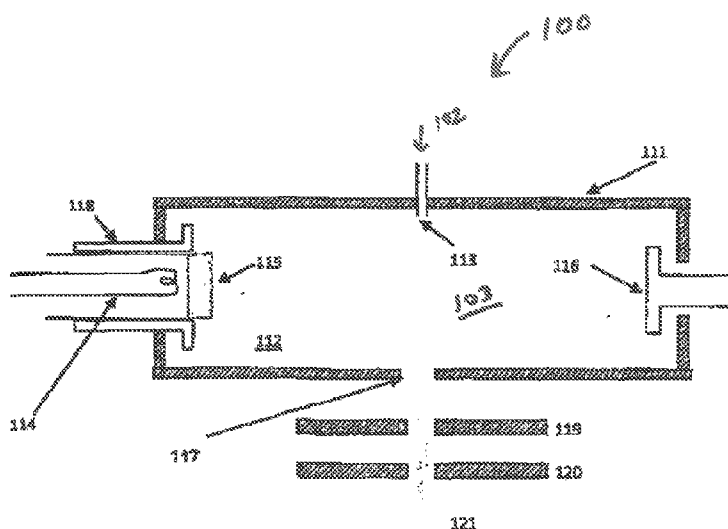
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(54) Title: SUPPLY SOURCE AND METHOD FOR ENRICHED SELENIUM ION IMPLANTATION



Schematic of an ion source apparatus

FIG. 1

(57) Abstract: A novel method for ion im-
planting isotopically enriched selenium
containing source material is provided.
The source material is selected and en-
riched in a specific mass isotope of sele-
nium, whereby the enrichment is above nat-
ural abundance levels. The inventive
method allows reduced gas consumption
and reduced waste. The source material is
preferably stored and delivered from a
sub-atmospheric storage and delivery
device to enhance safety and reliability
during the selenium ion implantation pro-
cess.



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